

# SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

EMH2408 —

N-Channel Silicon MOSFET General-Purpose Switching Device Applications

## Features

- The EMH2408 incorporates a N-channel MOSFET that feature low ON-resistance and ultrahigh-speed switching, thereby enabling high-density mounting
- 1.8V drive
- Halogen free compliance

# **Specifications**

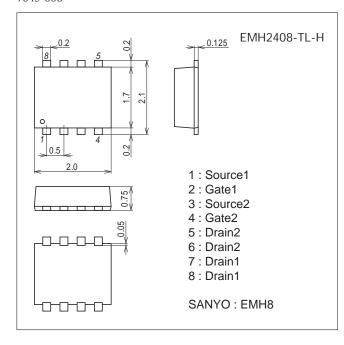
#### Absolute Maximum Ratings at Ta=25°C

| Parameter                   | Symbol           | Conditions  | Ratings     | Unit |
|-----------------------------|------------------|---|-------------|------|
| Drain-to-Source Voltage     | V <sub>DSS</sub> |   | 20          | V    |
| Gate-to-Source Voltage      | V <sub>GSS</sub> |   | ±12         | V    |
| Drain Current (DC)          | ID               |   | 4           | А    |
| Drain Current (Pulse)       | IDP              | PW≤10μs, duty cycle≤1%  | 16          | А    |
| Allowable Power Dissipation | PD               | When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm) 1unit | 1.0         | W    |
| Total Dissipation           | PT               | When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm)       | 1.2         | W    |
| Channel Temperature         | Tch              |   | 150         | °C   |
| Storage Temperature         | Tstg             |   | -55 to +150 | °C   |

This product is designed to "ESD immunity  $< 200V^*$ ", so please take care when handling. \* Machine Model

#### Package Dimensions

unit : mm (typ) 7045-006



#### Product & Package Information

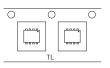
- : EMH8
- JEITA, JEDEC

• Package

• Minimum Packing Quantity : 3,000 pcs./reel

: -

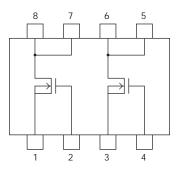
#### Packing Type : TL





Marking

#### **Electrical Connection**

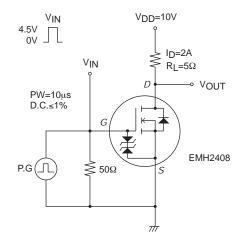


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| Decemeter                                  | Cumbral   |   |     | 11-14   |     |      |
|--|---|---|-----|---------|-----|------|
| Parameter                                  | Symbol  | Conditions                                | min | typ max |     | Unit |
| Drain-to-Source Breakdown Voltage          | V(BR)DSS  | ID=1mA, VGS=0V                            | 20  |         |     | V    |
| Zero-Gate Voltage Drain Current            | IDSS  | V <sub>DS</sub> =20V, V <sub>GS</sub> =0V |     |         | 1   | μΑ   |
| Gate-to-Source Leakage Current             | IGSS  | V <sub>GS</sub> =±8V, V <sub>DS</sub> =0V |     |         | ±10 | μΑ   |
| Cutoff Voltage                             | V <sub>GS</sub> (off)   | V <sub>DS</sub> =10V, I <sub>D</sub> =1mA | 0.4 |         | 1.3 | V    |
| Forward Transfer Admittance                | yfs   | VDS=10V, ID=2A                            | 2.0 | 3.4     |     | S    |
|  | R <sub>DS</sub> (on)1   | ID=4A, VGS=4.5V                           |     | 34      | 45  | mΩ   |
| Static Drain-to-Source On-State Resistance | R <sub>DS</sub> (on)2   | ID=1A, VGS=2.5V                           |     | 49      | 67  | mΩ   |
|  | R <sub>DS</sub> (on)3   | ID=0.5A, VGS=1.8V                         |     | 74      | 115 | mΩ   |
| Input Capacitance                          | Ciss  |   |     | 345     |     | pF   |
| Output Capacitance                         | Coss  | V <sub>DS</sub> =10V, f=1MHz              |     | 67      |     | pF   |
| Reverse Transfer Capacitance               | Crss  |   |     | 52      |     | pF   |
| Turn-ON Delay Time                         | t <sub>d</sub> (on)   |   |     | 9.2     |     | ns   |
| Rise Time                                  | tr  |   |     | 60      |     | ns   |
| Turn-OFF Delay Time                        | t <sub>d</sub> (off)  | See specified Test Circuit.               |     | 30      |     | ns   |
| Fall Time                                  | tf  |   |     | 38      |     | ns   |
| Total Gate Charge                          | Qg  |   |     | 4.7     |     | nC   |
| Gate-to-Source Charge                      | Qgs V <sub>DS</sub> =10V, V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A |   |     | 0.65    |     | nC   |
| Gate-to-Drain "Miller" Charge              | Qgd   | 1   |     | 1.6     |     | nC   |
| Diode Forward Voltage                      | VSD   | IS=4A, VGS=0V                             |     | 0.8     | 1.2 | V    |

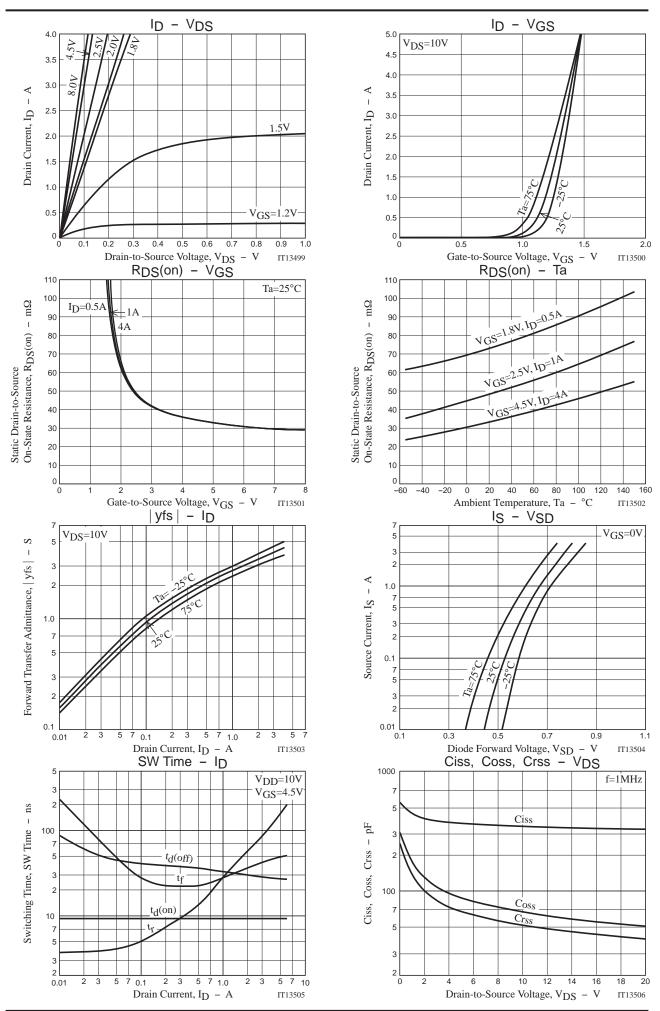
## Electrical Characteristics at Ta=25°C

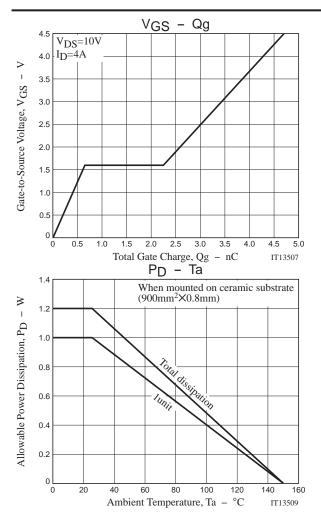
# Switching Time Test Circuit

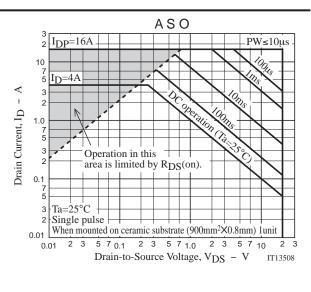


#### **Ordering Information**

| Device       | Package | Shipping       | memo                     |  |  |
|--------------|---------|----------------|--------------------------|--|--|
| EMH2408-TL-H | EMH8    | 3,000pcs./reel | Pb Free and Halogen Free |  |  |







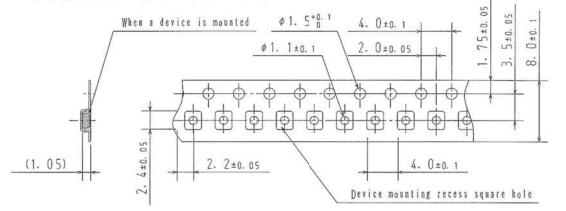
## Embossed Taping Specification EMH2408-TL-H

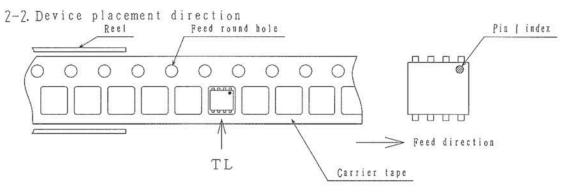
1. Packing Format

| Package Name | Carrier Tape |             | imum Number of<br>es contained (pcs) |           | Packing format                                      |                     |                         |   |
|--------------|--------------|-------------|--------------------------------------|-----------|---|---------------------|-------------------------|---|
|              | Type         | Reel        | [nner box                            | Quter box | Inn   | er BOX              | (C-1)                   | Outer BOX (A-7)   |
| EMH8         | MCP4         | 3, 000      | 15,000                               | 90,000    | 5 reel  | s contain           | ed                      | 6 inner boxes contained   |
|              |              |             |                                      |           | Dinen   | sions:mm            | (externa                | 1) Dimensions:mm (external)   |
|              |              |             |                                      |           | 18  | 3×72>               | < 185                   | 440×195×210   |
|              |              |             | Reel                                 | label, [  | (nner b   | ox label            |                         | er box label  |
| Packing me   | thod         |             |                                      | (u 1      | nit:m   | n)                  | The                     | s a label at the time of factory shipmen<br>form of a label may change in physical<br>ribution process. |
| •            |              |             | -                                    | 6         | 59  |                     |                         | 108   |
|              | Orig         | No.<br>tity |                                      |           | Initiation III III<br>IIIIIIIIIIIIIIIIIIIIIIIIIIIII | *****)<br>escriptio | n shows                 | TYPE CODE   |
|              |              |             | []<br>[]                             | Label     |   | PARTICIPATION - A   | Phase                   |   |
|              |              |             |                                      | LEAD FRE  |   | JEITA I             | in minimum and a second | A   |
|              |              |             |                                      | LEAD FRE  | EE 4  | JEITA I             | hase 3                  |   |

# 2. Taping configuration

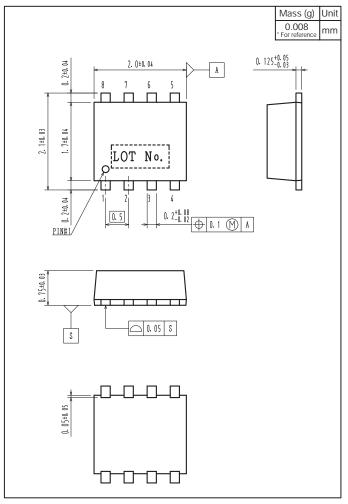
2-1. Carrier tape size (unit:mm)



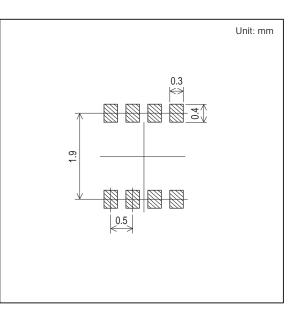


Those with pin 1 index on the feed hole side ..... TL

# Outline Drawing EMH2408-TL-H



# Land Pattern Example



Note on usage : Since the EMH2408 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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